

# BFP740ESD

Robust High Performance Low Noise Bipolar RF Transistor

## Data Sheet

Revision 1.0, 2010-06-29

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**BFP740ESD, Robust High Performance Low Noise Bipolar RF Transistor**

**Revision History: 2010-06-29, Revision 1.0**

**Previous Revision:**

Page	Subjects (major changes since last revision)

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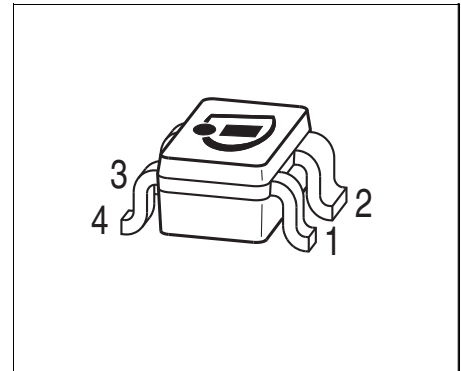
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## 1 Features

- Robust high performance low noise amplifier based on Infineon’s reliable, high volume SiGe:C wafer technology
- 2 kV ESD robustness (HBM) due to integrated protection circuits
- High maximum RF input power of 21 dBm
- 0.65 dB minimum noise figure typical at 2.4 GHz, 0.9 dB at 5.5 GHz, 6 mA
- 25.5 dB maximum gain ( $G_{ma}$ ,  $G_{ms}$ ) typical at 2.4 GHz, 18.5 dB at 5.5 GHz, 25 mA
- 24 dBm  $OIP_3$  typical at 5.5 GHz, 25 mA
- Accurate SPICE GP model available to enable effective design in process (see chapter 6)
- Easy to use, Pb- and halogen free (RoHS compliant) standard package with visible leads



## Applications

As Low Noise Amplifier (LNA) in

- Mobile, portable and fixed connectivity applications: WLAN 802.11a/b/g/n, WiMax 2.5/3.5/5 GHz, UWB, Bluetooth
- Satellite communication systems: Navigation systems (GPS, Glonass), satellite radio (SDARs, DAB) and C-band LNB
- Multimedia applications such as mobile/portable TV, CATV, FM Radio
- 3G/4G UMTS/LTE mobile phone applications
- ISM applications like RKE, AMR and Zigbee, as well as for emerging wireless applications

As discrete active mixer, amplifier in VCOs and buffer amplifier

**Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions**

Product Name	Package	Pin Configuration				Marking
BFP740ESD	SOT343	1 = B	2 = E	3 = C	4 = E	T7s



## 2 Product Brief

The BFP740ESD is a Silicon Germanium Carbon (SiGe:C) NPN Heterojunction wideband Bipolar RF Transistor (HBT) in a plastic dual emitter standard package with visible leads. The device is fitted with internal protection circuits, which enhance robustness against ESD and high RF input power strongly. The device combines robustness with very high RF gain and lowest noise figure at low operation current for use in a wide range of wireless applications.

The BFP740ESD is especially well-suited for portable battery-powered applications in which reduced power consumption is a key requirement. Device design supports collector voltages up to 4.2 V.

**Table 1 Quick Reference DC Characteristics at  $T_A = 25^\circ\text{C}$**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	4.2	4.7	–	V	$I_C = 1 \text{ mA}$ , $I_B = 0$ Open base
Collector base leakage current	$I_{CBO}$	–	–	400	nA	$V_{CB} = 2 \text{ V}$ , $I_E = 0$ Open emitter
DC current gain	$h_{FE}$	160	250	400		$V_{CE} = 3 \text{ V}$ , $I_C = 25 \text{ mA}$
Collector current	$I_C$	–	–	45	mA	
Total power dissipation	$P_{tot}$	–	–	160	mW	$T_S \leq 98^\circ\text{C}$



**Table 2 Quick Reference AC Characteristics at  $T_A = 25^\circ\text{C}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transition frequency	$f_T$	–	45	–	GHz	$V_{CE} = 3\text{ V}, I_C = 25\text{ mA}$ $f = 2\text{ GHz}$
<b><math>V_{CE} = 3\text{ V}, f = 2.4\text{ GHz}</math></b>						
<b>Maximum power gain</b>						
Low noise operation point	$G_{ms}$	–	22	–	dB	$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	25.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>						
Low noise operation point	$S_{21}$	–	19.5	–	dB	$Z_S = Z_L = 50\ \Omega$ $I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	22	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>						
Minimum noise figure	$NF_{min}$	–	0.65	–	dB	$Z_S = Z_{opt}$ $I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	20	–		$I_C = 6\text{ mA}$
<b>Linearity</b>						
1 dB gain compression point	$OP_{1dB}$	–	10.5	–	dBm	$Z_S = Z_L = 50\ \Omega$ $I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	25	–		$I_C = 25\text{ mA}$
<b><math>V_{CE} = 3\text{ V}, f = 5.5\text{ GHz}</math></b>						
<b>Maximum power gain</b>						
Low noise operation point	$G_{ms}$	–	19	–	dB	$I_C = 6\text{ mA}$
High linearity operation point	$G_{ma}$	–	18.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>						
Low noise operation point	$S_{21}$	–	13	–	dB	$Z_S = Z_L = 50\ \Omega$ $I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	14.5	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>						
Minimum noise figure	$NF_{min}$	–	0.9	–	dB	$Z_S = Z_{opt}$ $I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	13.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>						
1 dB gain compression point	$OP_{1dB}$	–	10	–	dBm	$Z_S = Z_L = 50\ \Omega$ $I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	24	–		$I_C = 25\text{ mA}$

### 3 Maximum Ratings

**Table 3 Maximum Ratings at  $T_A = 25^\circ\text{C}$  (unless otherwise specified)**

Parameter	Symbol	Values		Unit	Note / Test Condition
		Min.	Max.		
Collector emitter voltage	$V_{\text{CEO}}$	–	4.2	V	Open base $T_A = 25^\circ\text{C}$
		–	3.7	V	$T_A = -55^\circ\text{C}$
Collector emitter voltage <sup>1)</sup>	$V_{\text{CBO}}$	–	4.9	V	Open emitter $T_A = 25^\circ\text{C}$
		–	4.4	V	$T_A = -55^\circ\text{C}$
Collector emitter voltage <sup>2)</sup>	$V_{\text{CES}}$	–	4.2	V	Emitter / base shortened $T_A = 25^\circ\text{C}$
		–	3.7	V	$T_A = -55^\circ\text{C}$
Base current <sup>3)</sup>	$I_B$	-10	5	mA	–
Collector current	$I_C$	–	45	mA	–
RF input power	$P_{\text{RFIn}}$	–	21	dBm	–
ESD stress pulse <sup>4)</sup>	$V_{\text{ESD}}$	-2	2	kV	HBM, all pins, acc. to JESD22-A114
Total power dissipation <sup>5)</sup>	$P_{\text{tot}}$	–	160	mW	$T_S \leq 98^\circ\text{C}$
Junction temperature	$T_J$	–	150	$^\circ\text{C}$	–
Storage temperature	$T_{\text{Stg}}$	-55	150	$^\circ\text{C}$	–

1) Low  $V_{\text{CBO}}$  due to integrated protection circuits

2)  $V_{\text{CES}}$  is identical to  $V_{\text{CEO}}$  due to integrated protection circuits.

3) Sustainable reverse bias current is high due to integrated protection circuits.

4) ESD robustness is high due to integrated protection circuits.

5)  $T_S$  is the soldering point temperature.  $T_S$  measured on the emitter lead at the soldering point of the pcb.

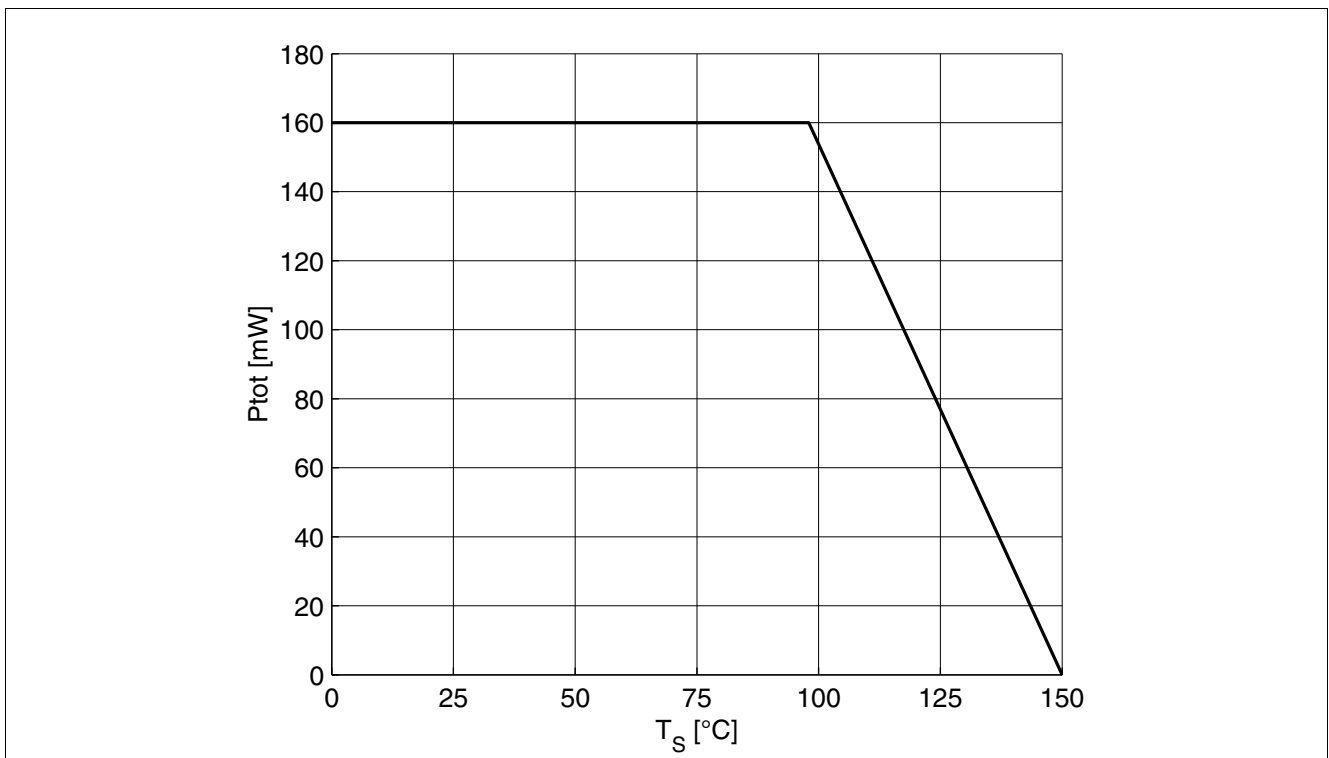
**Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.**

## 4 Thermal Characteristics

**Table 4 Thermal Resistance**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	–	325	–	K/W	–

1) For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance AN 077



**Figure 1 Total Power Dissipation  $P_{tot} = f(T_s)$**

## 5 Electrical Characteristics

### 5.1 DC Characteristics

**Table 5 DC Characteristics at  $T_A = 25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	4.2	4.7	–	V	$I_C = 1\text{ mA}$ , $I_B = 0$ Open base
Collector emitter leakage current	$I_{CES}$	–	–	400	nA	$V_{CE} = 2\text{ V}$ , $V_{BE} = 0$ Emitter/base shortened
Collector base leakage current	$I_{CBO}$	–	–	400	nA	$V_{CB} = 2\text{ V}$ , $I_E = 0$ Open emitter
Emitter base leakage current	$I_{EBO}$	–	–	10	$\mu\text{A}$	$V_{EB} = 0.5\text{ V}$ , $I_C = 0$ Open collector
DC current gain	$h_{FE}$	160	250	400		$V_{CE} = 3\text{ V}$ , $I_C = 25\text{ mA}$ Pulse measured

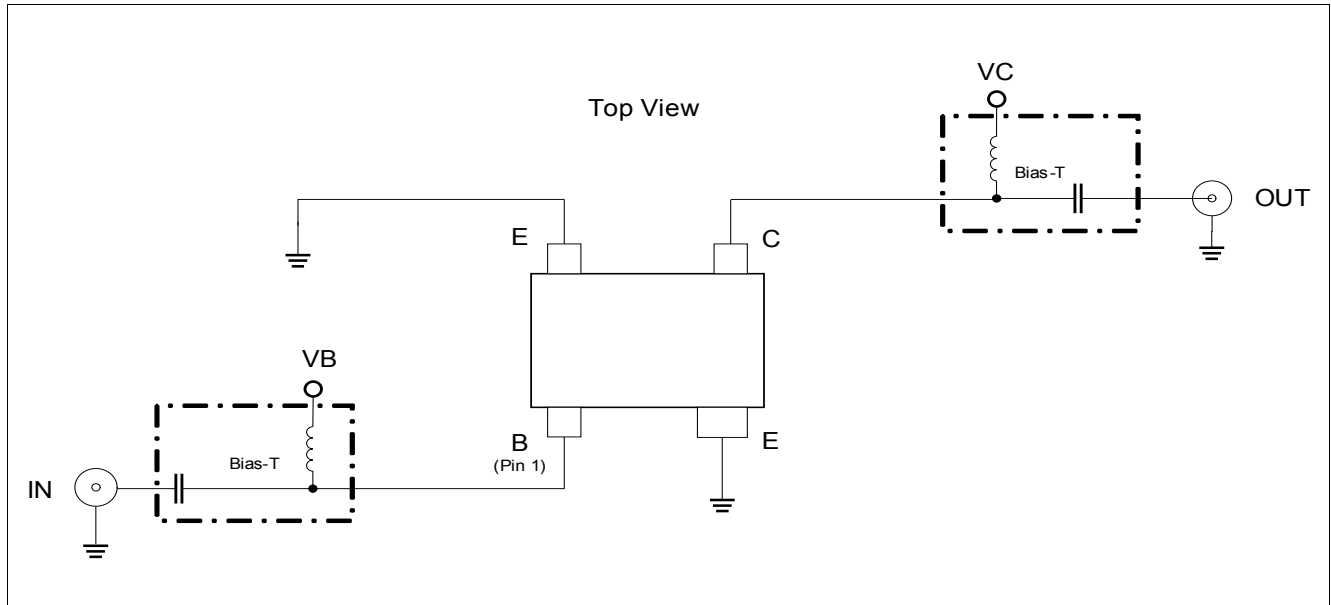
### 5.2 General AC Characteristics

**Table 6 General AC Characteristics at  $T_A = 25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Transition frequency	$f_T$	–	45	–	GHz	$V_{CE} = 3\text{ V}$ , $I_C = 25\text{ mA}$ $f = 2\text{ GHz}$
Collector base capacitance	$C_{CB}$	–	0.08	–	pF	$V_{CB} = 3\text{ V}$ , $V_{BE} = 0$ $f = 1\text{ MHz}$ Emitter grounded
Collector emitter capacitance	$C_{CE}$	–	0.45	–	pF	$V_{CE} = 3\text{ V}$ , $V_{BE} = 0$ $f = 1\text{ MHz}$ Base grounded
Emitter base capacitance	$C_{EB}$	–	0.55	–	pF	$V_{EB} = 0.4\text{ V}$ , $V_{CB} = 0$ $f = 1\text{ MHz}$ Collector grounded

### 5.3 Frequency Dependent AC Characteristics

Measurement setup is a test fixture with Bias T's in a 50 Ω system,  $T_A = 25\text{ °C}$



**Figure 2 BFP740ESD Testing Circuit**

**Table 7 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 150\text{ MHz}$**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	34	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	38.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\text{ }\Omega$
Low noise operation point	$S_{21}$	–	25	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	34	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.55	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	30.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\text{ }\Omega$
1 dB gain compression point	$OP_{1dB}$	–	9	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	23.5	–		$I_C = 25\text{ mA}$

**Electrical Characteristics**
**Table 8 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 450\text{ MHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	29	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	33.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	24.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	32	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.55	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	28.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	9.5	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	23.5	–		$I_C = 25\text{ mA}$

**Table 9 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 900\text{ MHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	26	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	30.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	23.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	29	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.55	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	25.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	9.5	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	24	–		$I_C = 25\text{ mA}$

**Electrical Characteristics**
**Table 10 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 1.5\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	23.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	28	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	22	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	25.5	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.6	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	23	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	10	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	24.5	–		$I_C = 25\text{ mA}$

**Table 11 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 1.9\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	22.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	26.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	21	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	24	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.6	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	21	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	10	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	25	–		$I_C = 25\text{ mA}$



**Electrical Characteristics**
**Table 12 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 2.4\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	22	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	25.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	19.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	22	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.65	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	20	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	10.5	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	25	–		$I_C = 25\text{ mA}$

**Table 13 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 3.5\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	20.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	23	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	17	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	19	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.7	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	16.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	10.5	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	24.5	–		$I_C = 25\text{ mA}$

**Electrical Characteristics**
**Table 14 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 5.5\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	19	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ma}$	–	18.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	13	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	14.5	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	0.9	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	13.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	10	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	24	–		$I_C = 25\text{ mA}$

**Table 15 AC Characteristics,  $V_{CE} = 3\text{ V}$ ,  $f = 10\text{ GHz}$** 

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
<b>Maximum power gain</b>					dB	
Low noise operation point	$G_{ms}$	–	14.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$G_{ms}$	–	14.5	–		$I_C = 25\text{ mA}$
<b>Transducer gain</b>					dB	$Z_S = Z_L = 50\ \Omega$
Low noise operation point	$S_{21}$	–	5.5	–		$I_C = 6\text{ mA}$
High linearity operation point	$S_{21}$	–	7.5	–		$I_C = 25\text{ mA}$
<b>Minimum noise figure</b>					dB	$Z_S = Z_{opt}$
Minimum noise figure	$NF_{min}$	–	1.8	–		$I_C = 6\text{ mA}$
Associated gain	$G_{ass}$	–	8.5	–		$I_C = 6\text{ mA}$
<b>Linearity</b>					dBm	$Z_S = Z_L = 50\ \Omega$
1 dB gain compression point	$OP_{1dB}$	–	7.5	–		$I_C = 25\text{ mA}$
3rd order intercept point	$OIP_3$	–	21	–		$I_C = 25\text{ mA}$

Note:

- $G_{ms} = |S_{21} / S_{12}|$  for  $k < 1$ ;  $G_{ma} = |S_{21} / S_{12}|(k - (k^2 - 1)^{1/2})$  for  $k > 1$
- In order to get the  $NF_{min}$  values stated in this chapter the test fixture losses have been subtracted from all measured results.
- $OIP_3$  value depends on termination of all intermodulation frequency components. Termination used for this measurement is  $50\ \Omega$  from 0.2 MHz to 12 GHz.

5.4 Characteristic DC Diagrams

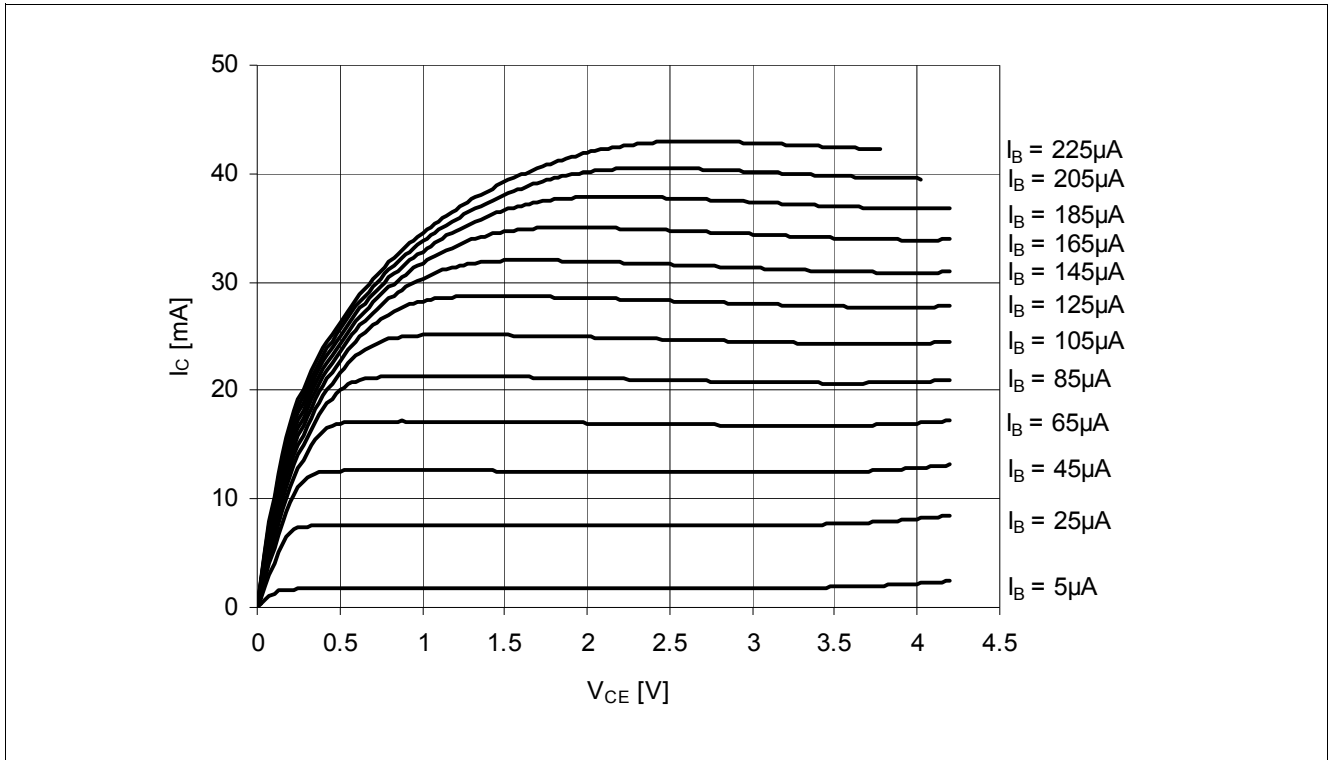


Figure 3 Collector Current vs. Collector Emitter Voltage  $I_C = f(V_{CE})$ ,  $I_B = \text{Parameter}$

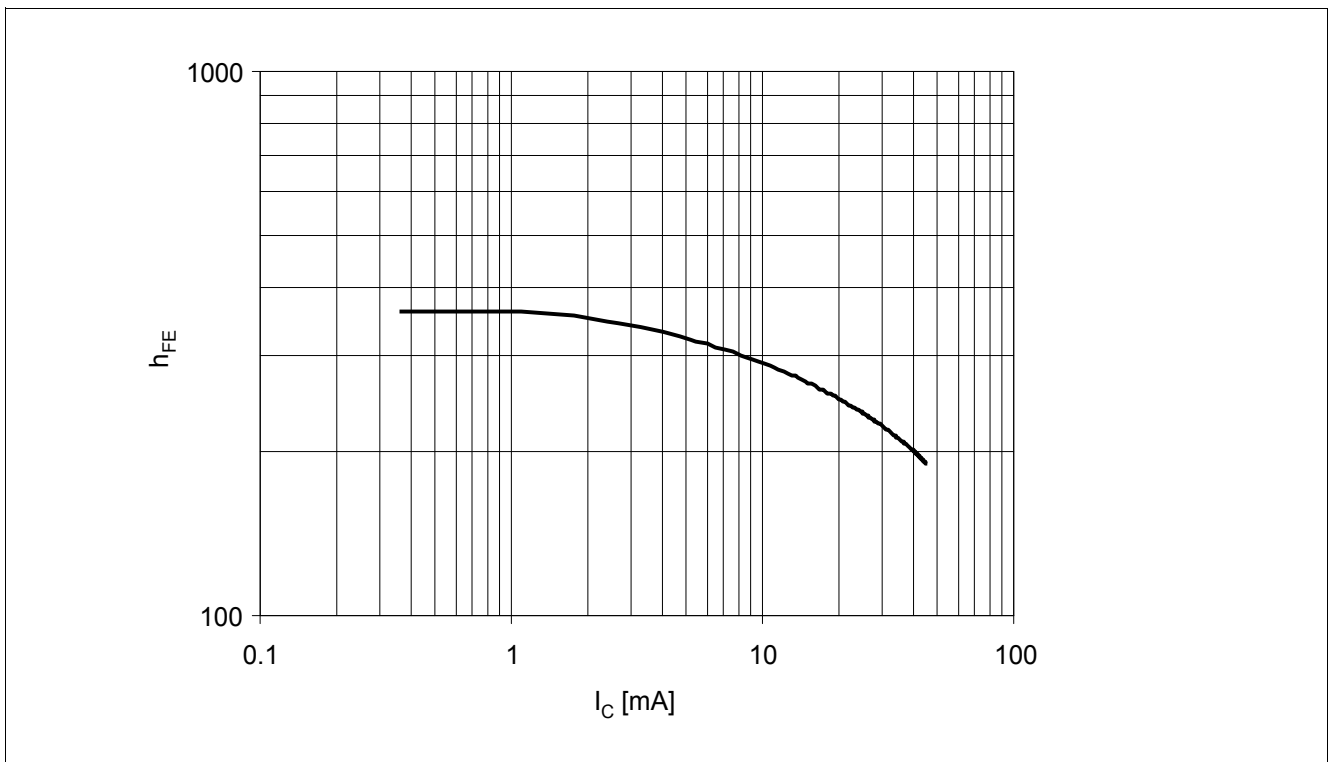


Figure 4 DC Current Gain  $h_{FE} = f(I_C)$ ,  $V_{CE} = 3 \text{ V}$

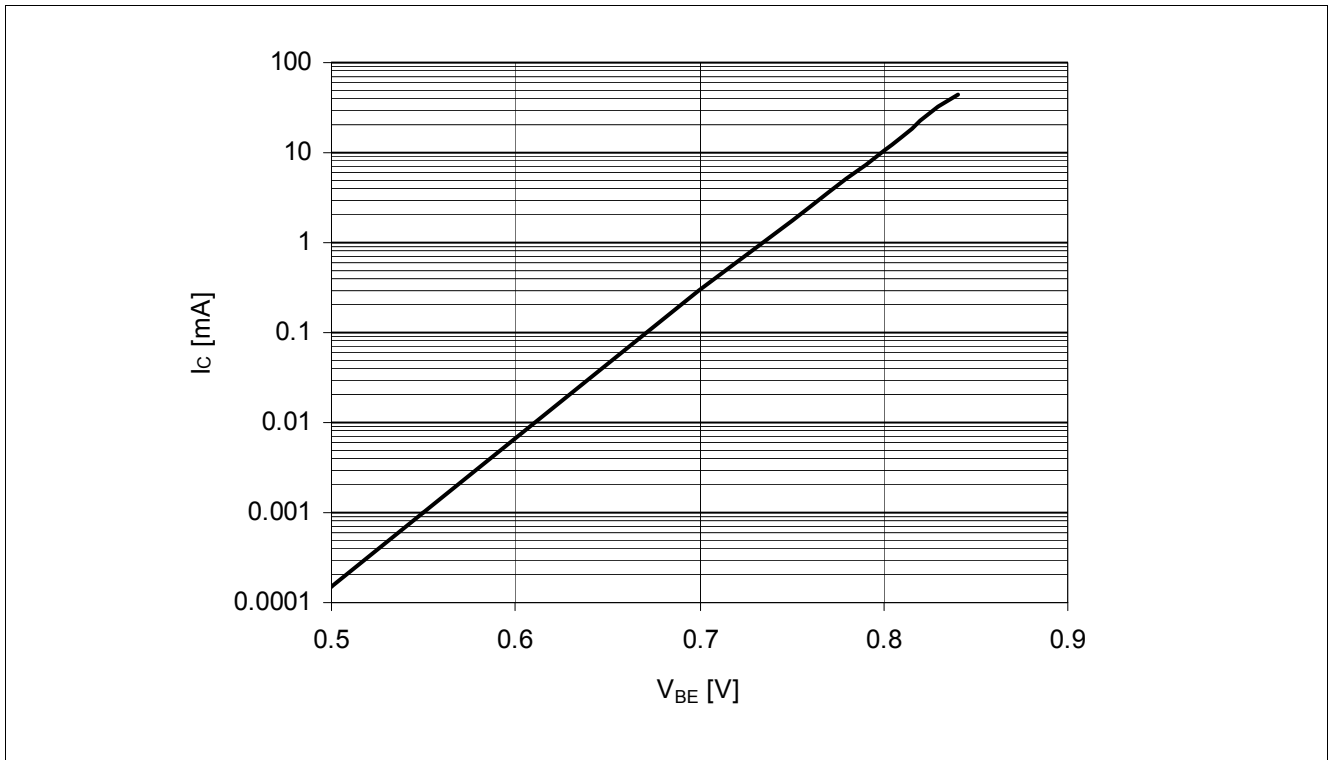


Figure 5 Collector Current vs. Base Emitter Voltage  $I_C = f(V_{BE})$ ,  $V_{CE} = 2\text{ V}$

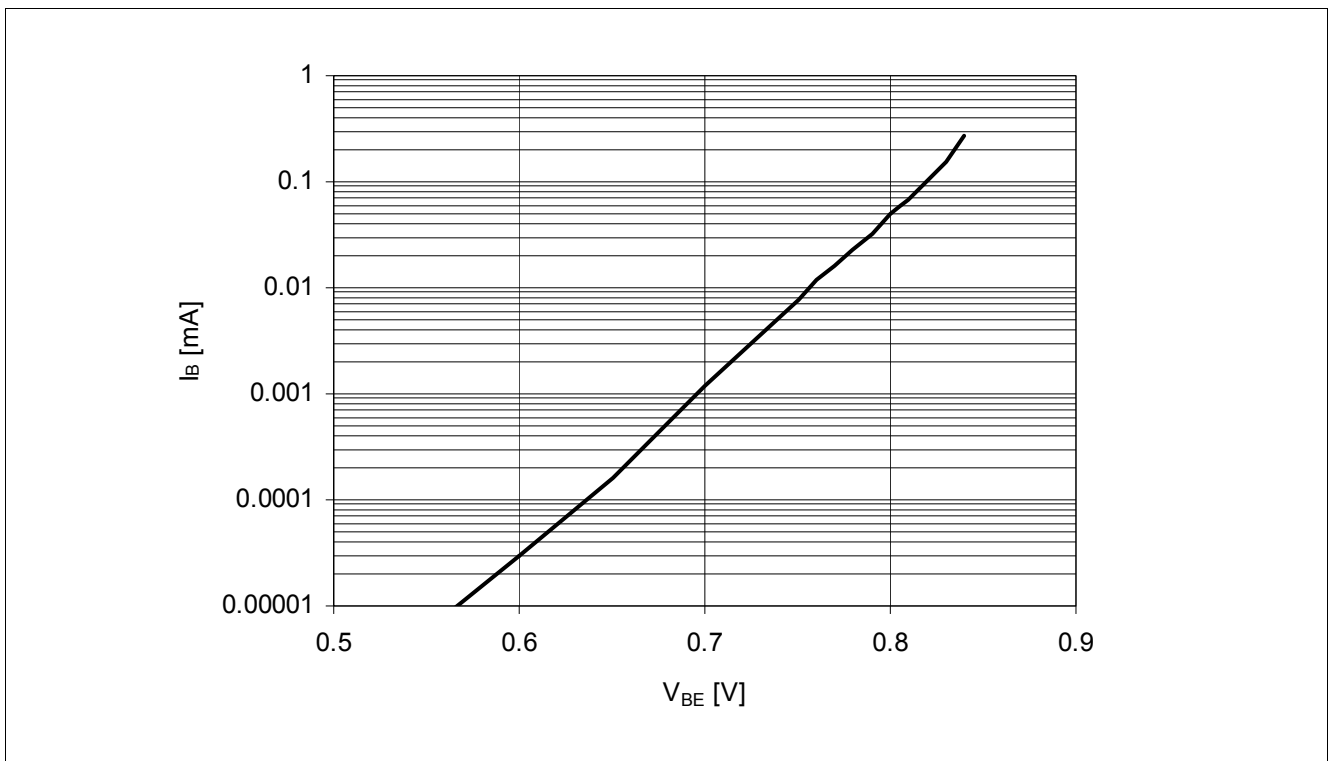


Figure 6 Base Current vs. Base Emitter Forward Voltage  $I_B = f(V_{BE})$ ,  $V_{CE} = 2\text{ V}$

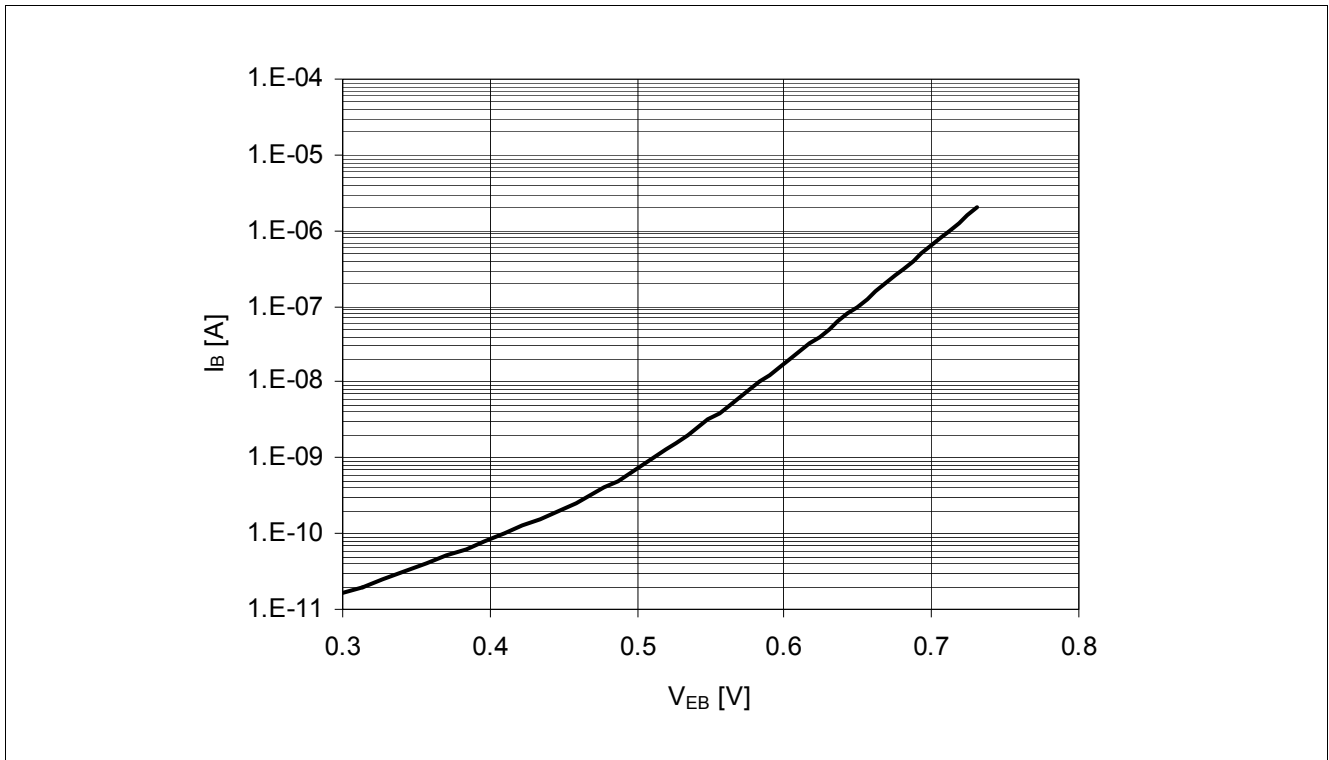


Figure 7 Base Current vs. Base Emitter Reverse Voltage  $I_B = f(V_{EB}), V_{CE} = 2\text{ V}$

### 5.5 Characteristic AC Diagrams

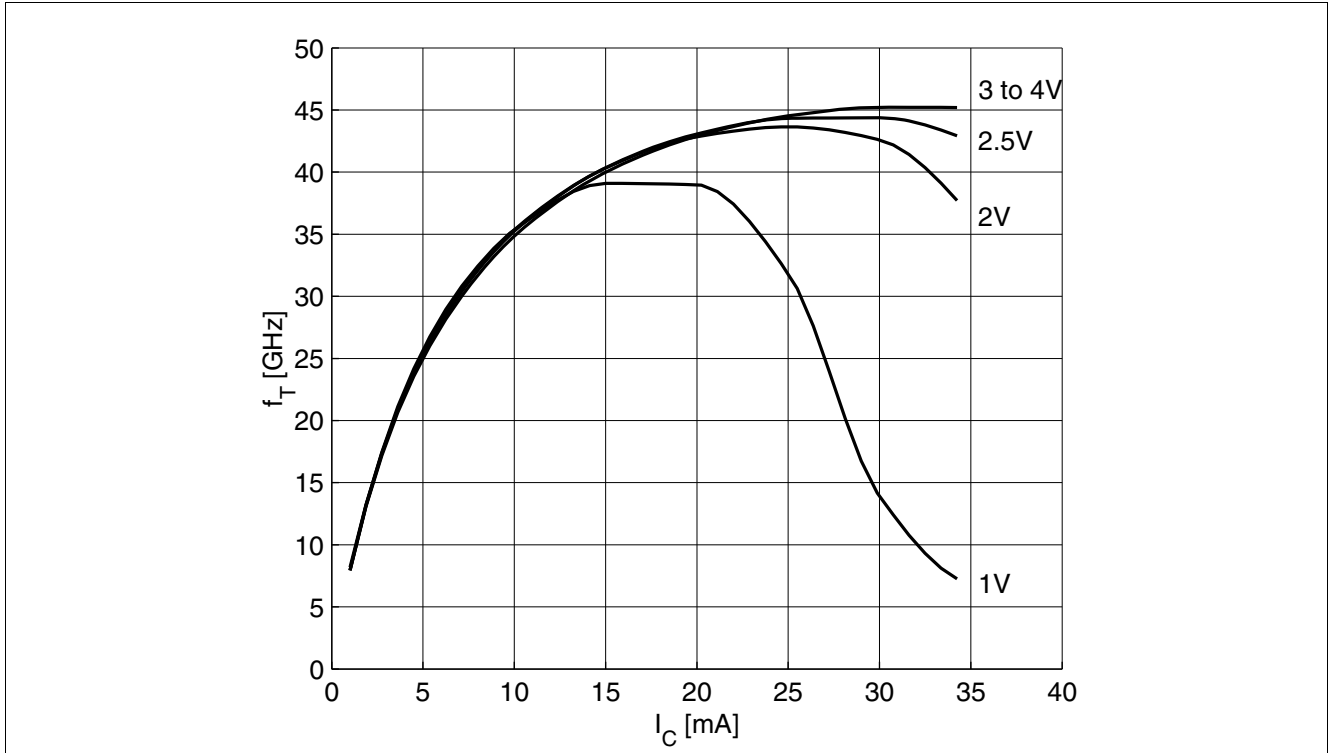


Figure 8 Transition Frequency  $f_T = f(I_C)$ ,  $f = 2$  GHz,  $V_{CE} = \text{Parameter}$

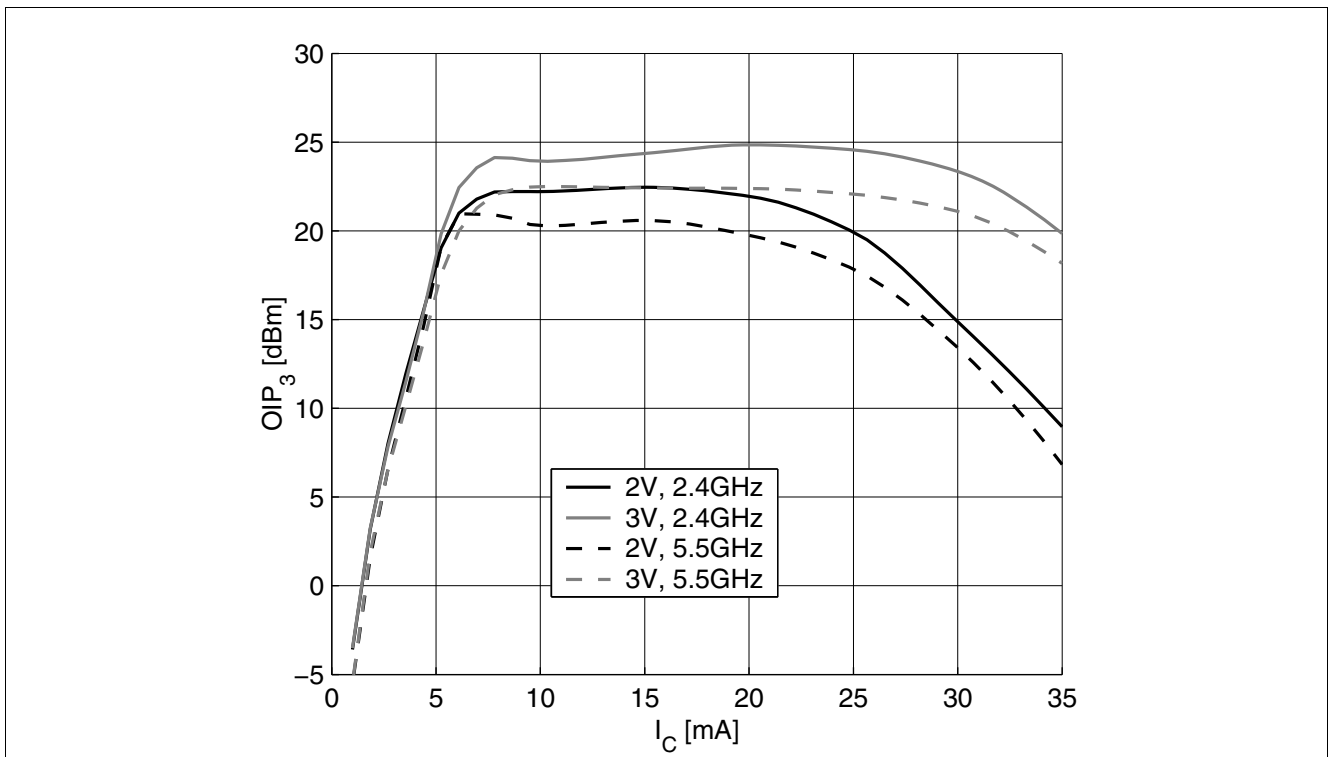


Figure 9 3rd Order Intercept Point  $OIP_3 = f(I_C)$ ,  $Z_S = Z_L = 50 \Omega$ ,  $V_{CE}, f = \text{Parameters}$

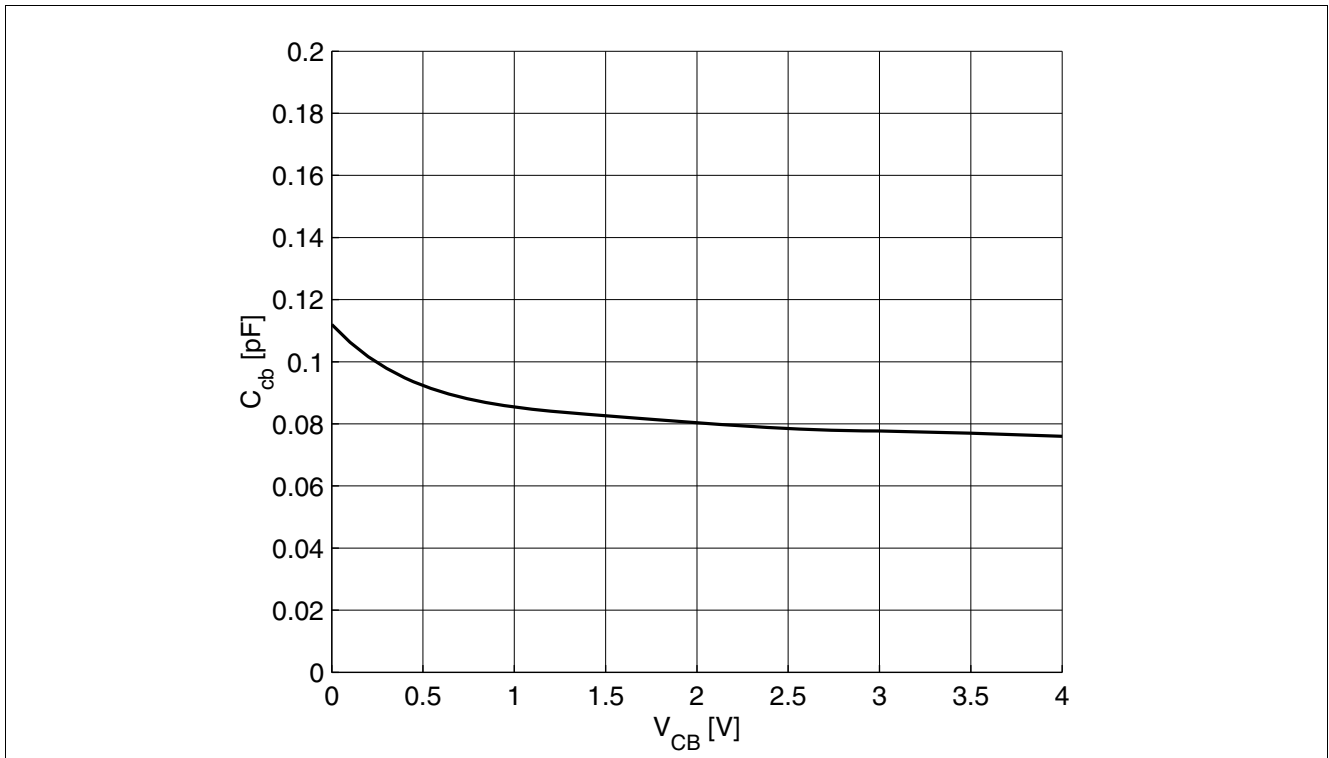


Figure 10 Collector Base Capacitance  $C_{CB} = f(V_{CB}), f = 1 \text{ MHz}$

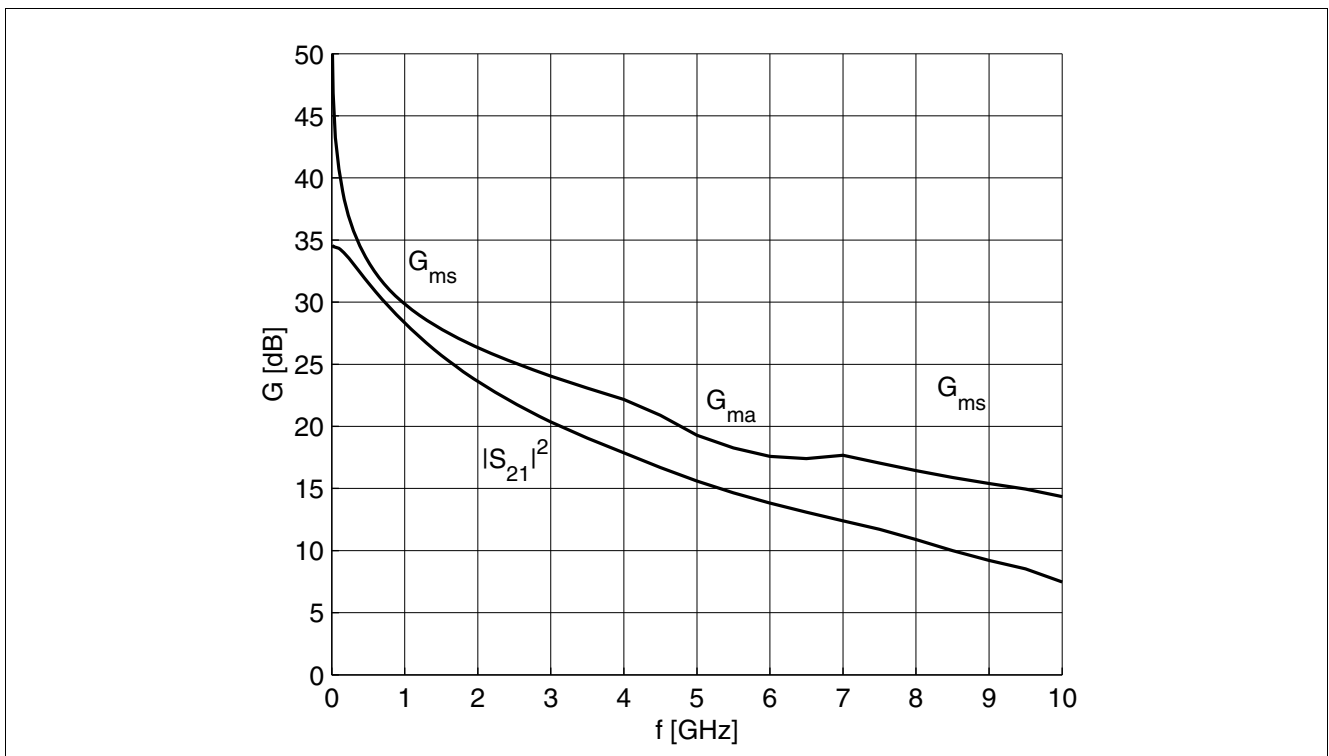


Figure 11 Gain  $G_{ma}, G_{ms}, |S_{21}|^2 = f(f), V_{CE} = 3 \text{ V}, I_C = 25 \text{ mA}$



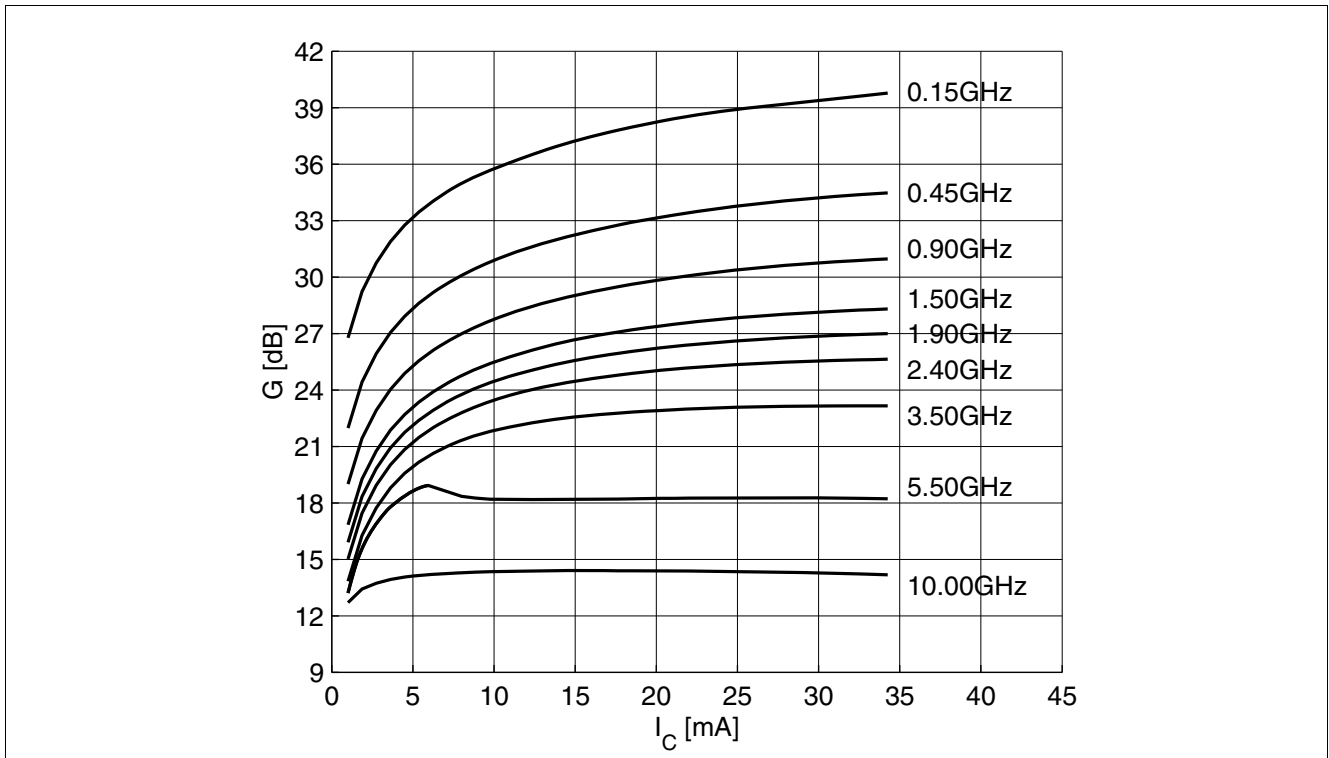


Figure 12 Maximum Power Gain  $G_{max} = f(I_C)$ ,  $V_{CE} = 3\text{ V}$ ,  $f = \text{Parameter in GHz}$

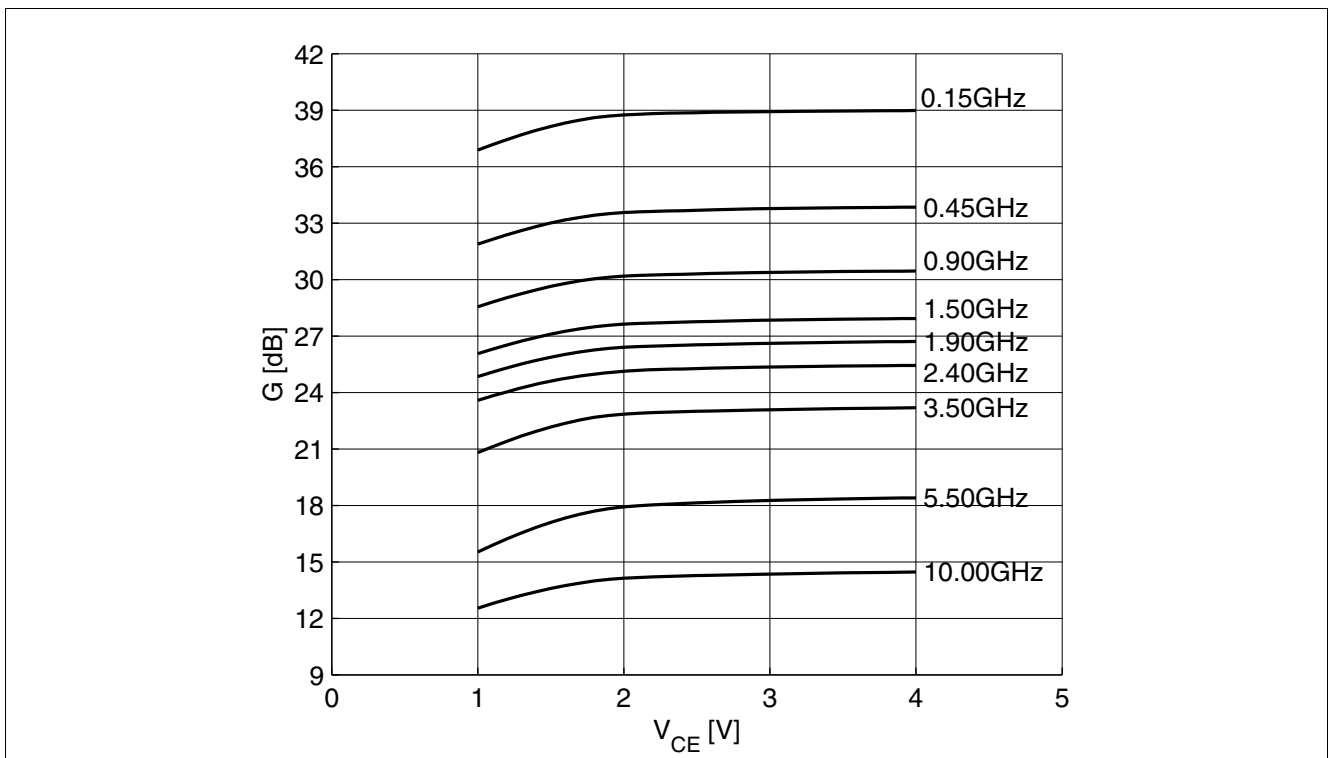


Figure 13 Maximum Power Gain  $G_{max} = f(V_{CE})$ ,  $I_C = 25\text{ mA}$ ,  $f = \text{Parameter in GHz}$

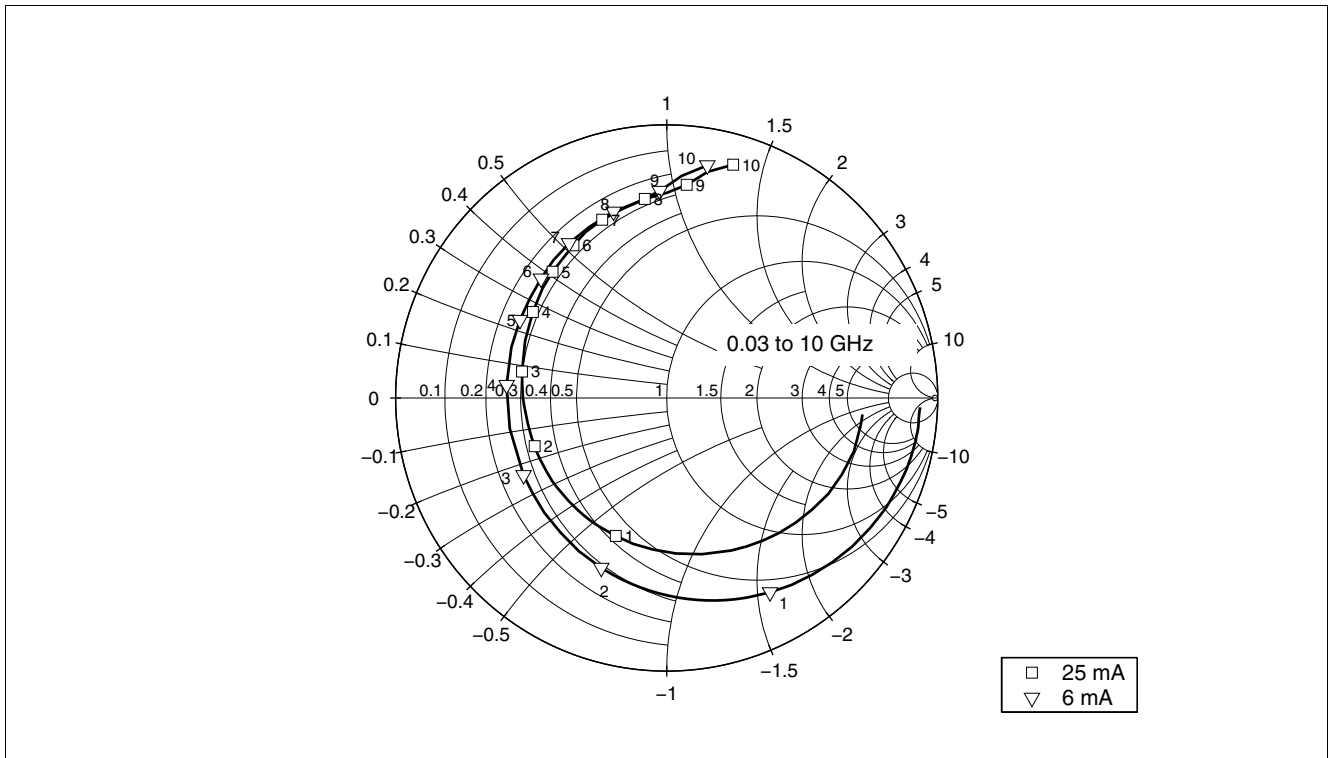


Figure 14 Input Matching  $S_{11} = f(f)$ ,  $V_{CE} = 3\text{ V}$ ,  $I_C = 6 / 25\text{ mA}$

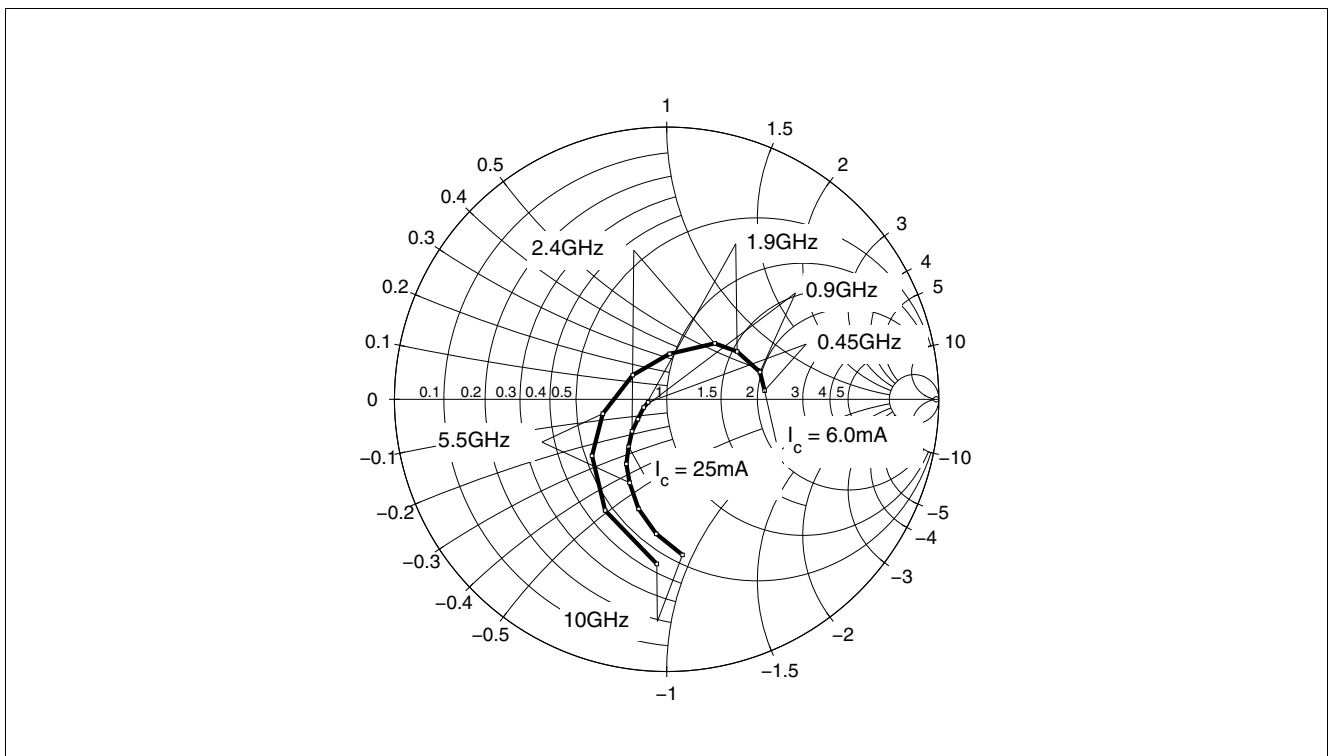


Figure 15 Source Impedance for Minimum Noise Figure  $Z_{opt} = f(f)$ ,  $V_{CE} = 3\text{ V}$ ,  $I_C = 6 / 25\text{ mA}$

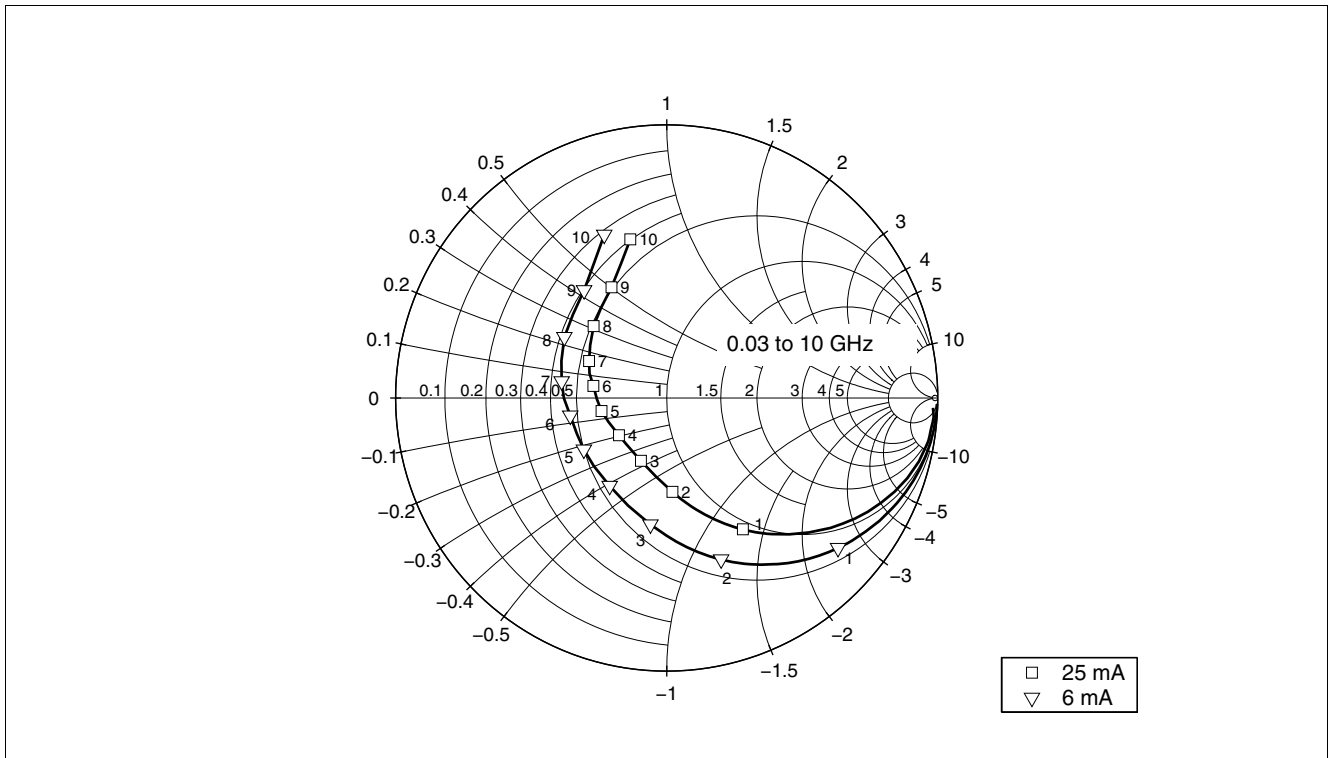


Figure 16 Output Matching  $S_{22} = f(f)$ ,  $V_{CE} = 3 \text{ V}$ ,  $I_C = 6 / 25 \text{ mA}$

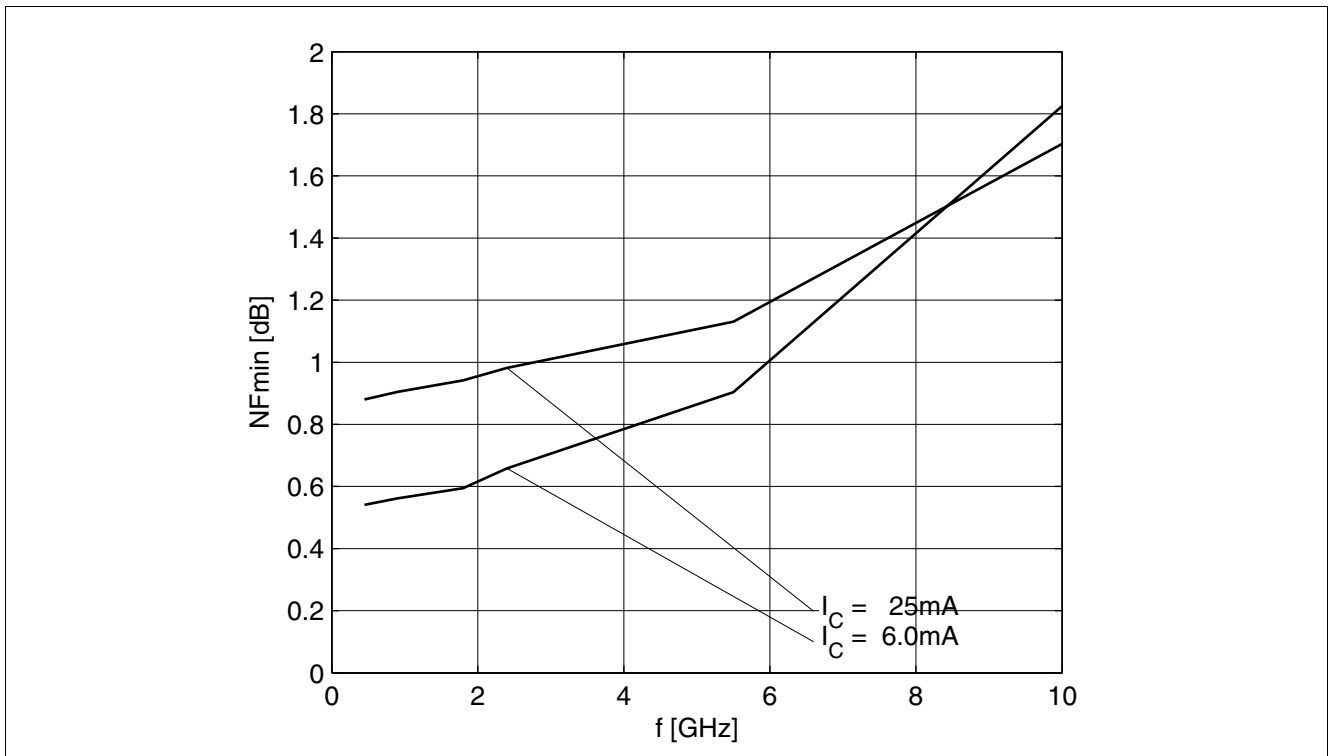


Figure 17 Noise Figure  $NF_{min} = f(f)$ ,  $V_{CE} = 3 \text{ V}$ ,  $I_C = 6 / 25 \text{ mA}$ ,  $Z_S = Z_{opt}$

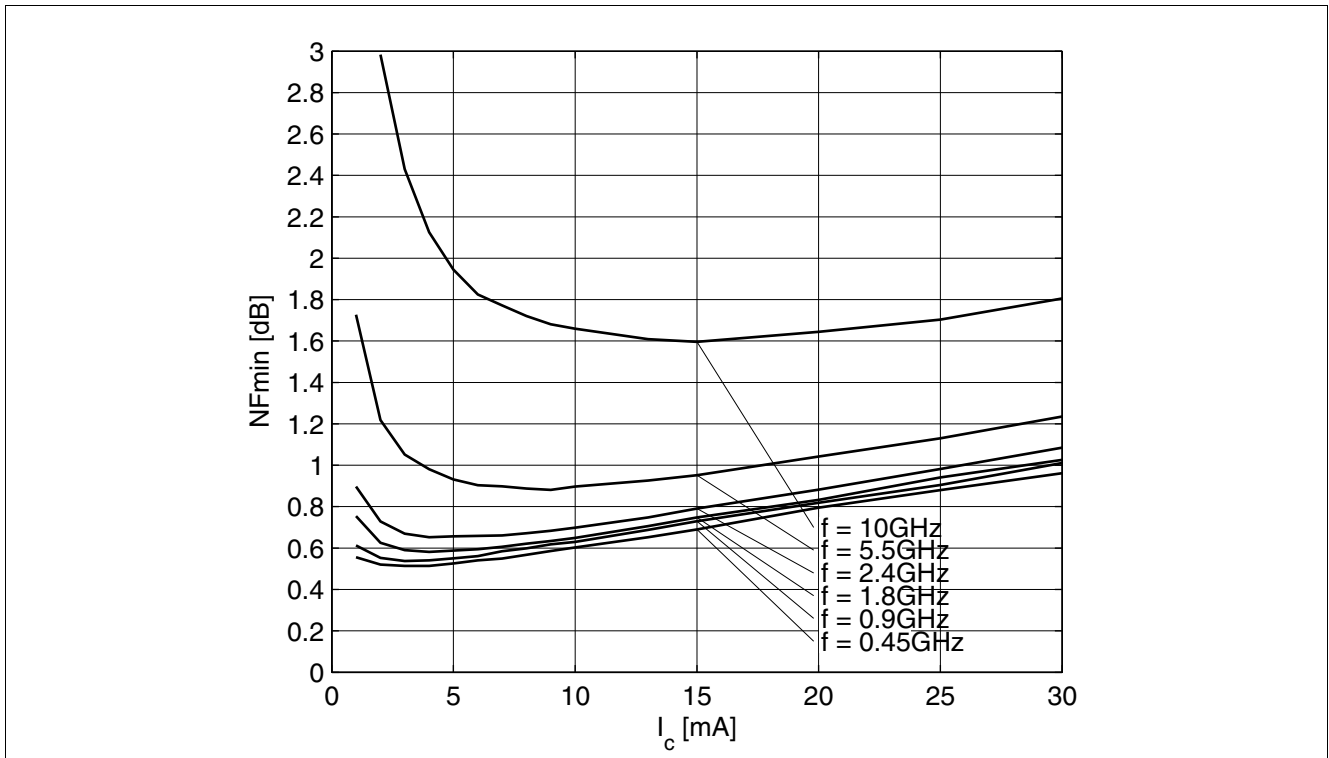


Figure 18 Noise Figure  $NF_{min} = f(I_C)$ ,  $V_{CE} = 3\text{ V}$ ,  $Z_S = Z_{opt}$ ,  $f = \text{Parameter in GHz}$

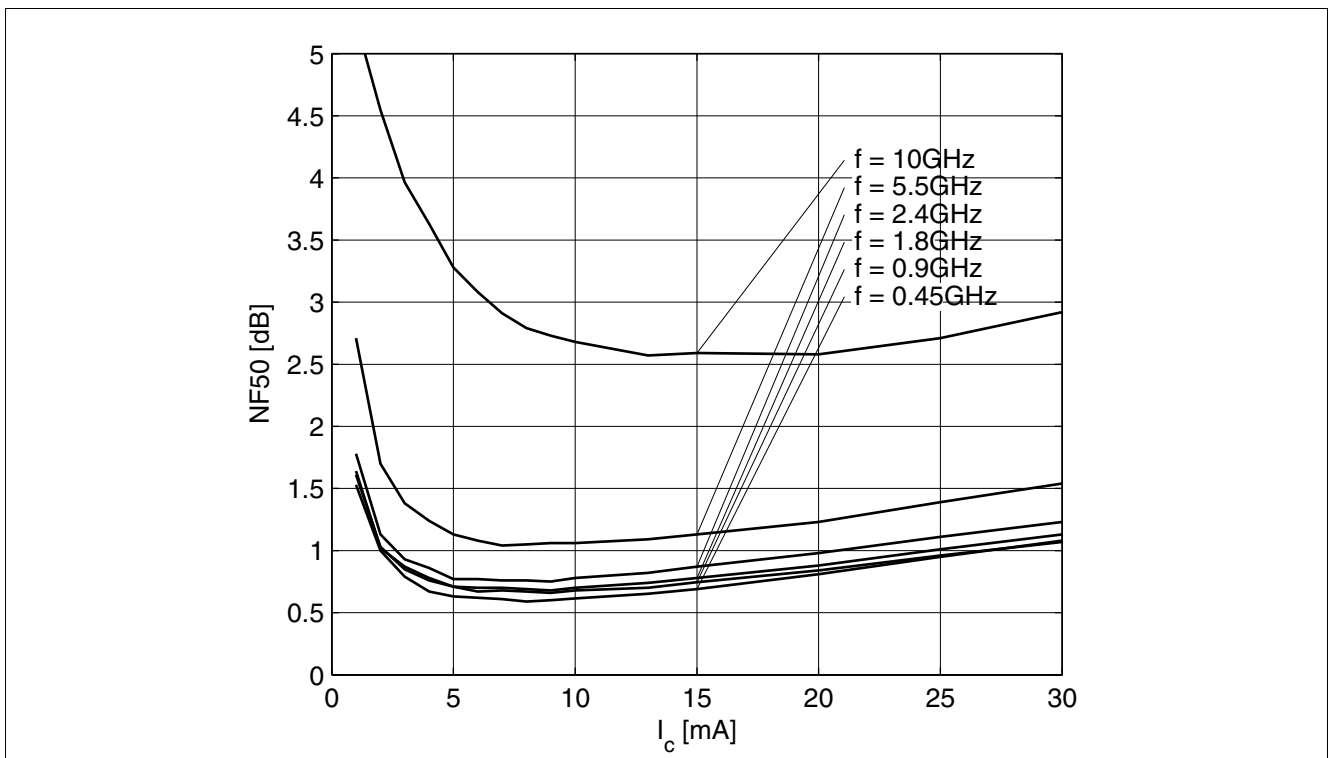


Figure 19 Noise Figure  $NF_{50} = f(I_C)$ ,  $V_{CE} = 3\text{ V}$ ,  $Z_S = 50\ \Omega$ ,  $f = \text{Parameter in GHz}$

Note: The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves.  $T_A = 25\text{ }^\circ\text{C}$

## 6 Simulation Data

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website: [www.infineon.com/rf.models](http://www.infineon.com/rf.models). Please consult our website and download the latest versions before actually starting your design.

You find the BFP740ESD SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC- and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device.

The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP740ESD SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.

## 7 Package Information SOT343

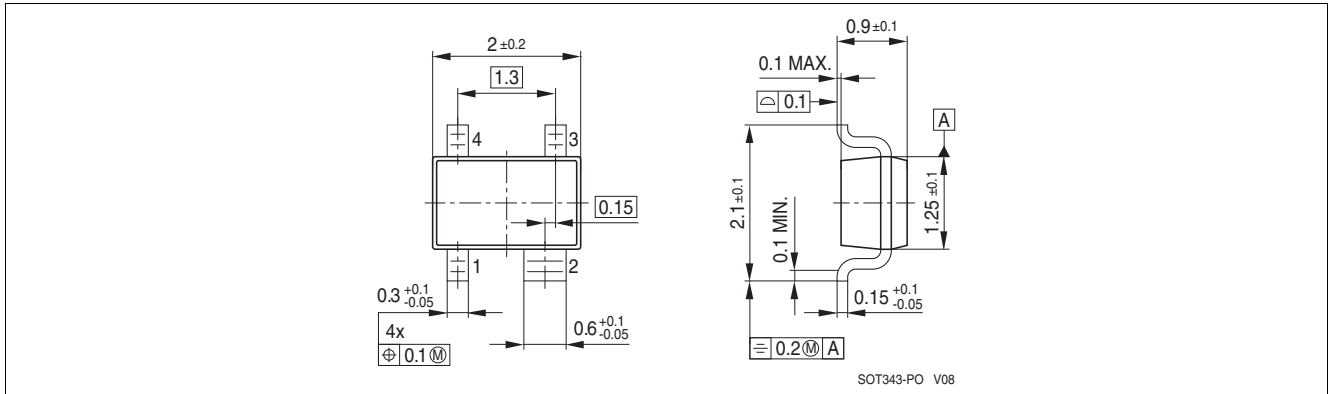


Figure 20 Package Outline

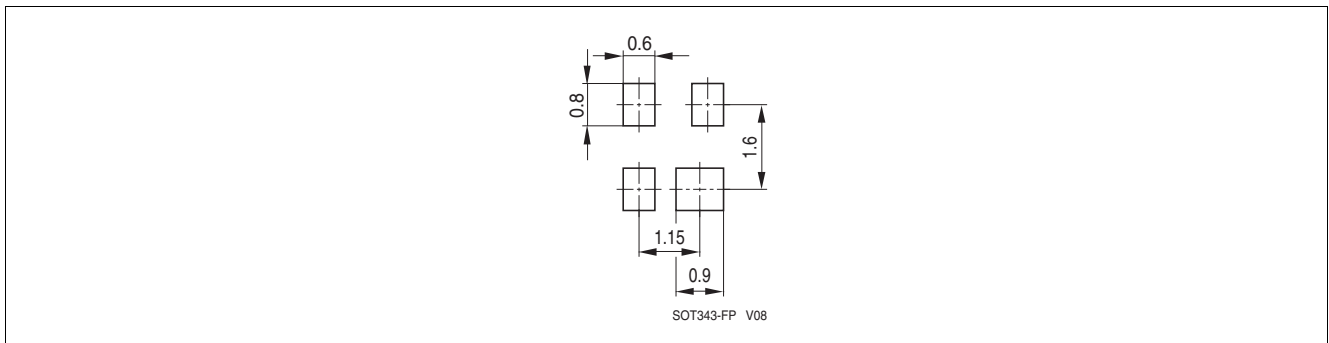


Figure 21 Package Foot Print

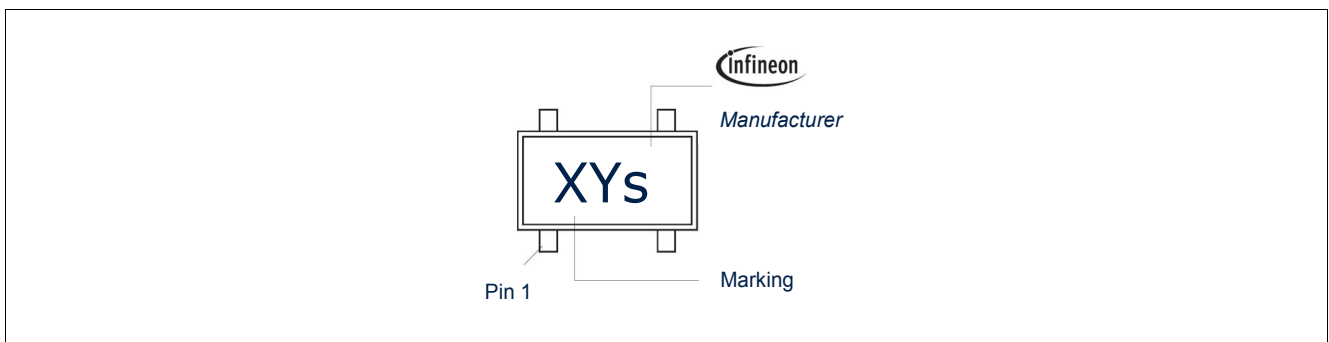


Figure 22 Marking Example (Marking BFP740ESD: T7s)

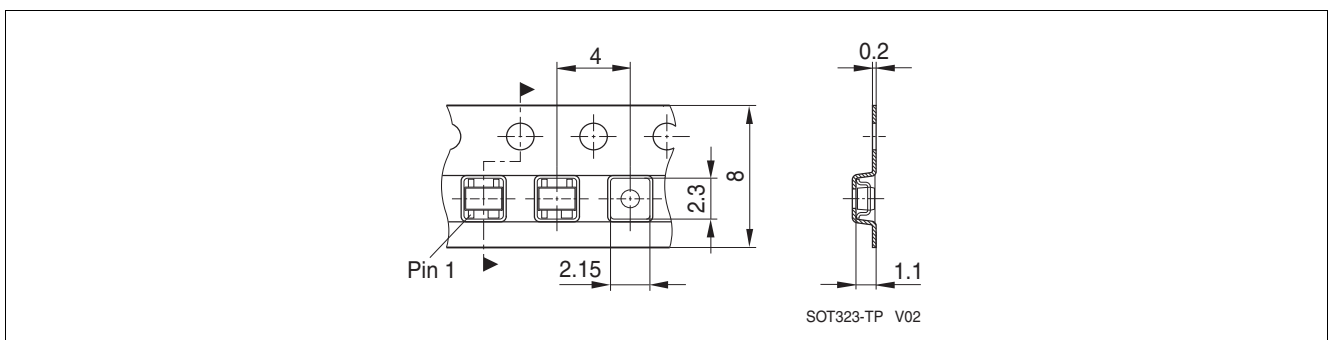


Figure 23 Tape Dimensions

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